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Low-voltage current noise in long quantum SINIS junctions

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The current noise in long SINIS junctions at low temperatures is sensitive to the population of the sub-gap states which is far from equilibrium even at low bias voltages. Nonequilibrium distribution establishes due to an interplay between voltage-driven inter-level Landau-Zener transitions and intra-level inelastic relaxation. We show that the Fano factor is enhanced drastically, being proportional to the number of times which particle can fly along the Andreev trajectory before it escapes from the level due to inelastic scattering. Combining the dc current and noise measurements one can fully characterize the non-equilibrium kinetics in SINIS junctions.

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Charge transport through mesoscopic normal-superconductor (NS) hybrid structures is a subject of intense current interest (see [1, 2] for a review). The multiple Andreev reflections (MAR) at the NS interfaces lead to several unusual features, in particular to the so-called sub-gap structure in the current-voltage (I-V) curves [3, 4, 5]. The electric current noise in NS hybrid systems provides information complementary to the dc-studies and exhibits properties that are essentially different from those of the contacts between the normal metals. In normal contacts, the shot noise induced by the Pauli correlation is relatively weak [6] and vanishes if the interface is ideal. In NS systems, on the contrary, Andreev scattering enhances reflection of electrons and results in a finite shot noise even when the contact itself is noiseless in the normal state [7]. The situation at low voltages is especially interesting: the interplay between the quasiparticle scattering and the superconducting coherence reveals an intricate structure of the non-equilibrium population of sub-gap states and leads to considerable enhancement of the noise [8, 9, 10, 11, 12].

In the present work we study the noise in a single-mode long SINIS junction (I stands for an insulator) where the length d of the normal conductor is much larger than the superconducting coherence length, but shorter than the inelastic mean-free path. This is an exemplary hybrid structure [13] where non-equilibrium dynamics is governed by inelastic scattering and voltage-driven Landau-Zener (LZ) transitions between Andreev sub-gap states. In particular, in a long junction where the number of the states involved in the transport is large, the LZ transitions lead to a significant increase in the dc current far above the critical Josephson current of the junction [14]. The noise properties of such systems are very informative. At finite temperature, the current noise is finite even in the absence of a dc bias voltage (and dissipation) and is related to thermal fluctuations in the occupancies of the sub-gap states [8, 9, 10]. The width of the zero-frequency peak in the noise spectrum is determined by the inelastic relaxation rate and thus provides an experimental tool for measuring its temperature dependence. We show that for low temperatures and small bias voltages the noise is controlled by the non-equilibrium population of the sub-gap states characterized by an *effective temperature* $T_{\rm eff}$ which is determined by the competition between the inelastic scattering and the voltage-driven inter-level LZ transitions; $T_{\rm eff}$ depends on the bias voltage and remains finite even at zero ambient temperature. At the same time, the dc current depends not only on $T_{\rm eff}$ but also on a LZ-controlled parameter that accounts for the charge transfer from the excited levels. For weak LZ processes, this parameter and thus the dc current are small. As a result, the ratio of the zero-frequency noise to the dc current, i. e., the Fano factor proportional to the fluctuating "effective charge" is increased drastically by a factor qualitatively different from that predicted in Refs. [8, 10] for short contacts. Since both the dc I-V curve and the noise spectrum depend on inelastic relaxation rate and on the LZ probabilities, the combined I-V and noise measurements enable detailed characterization of non-equilibrium dynamics in long SINIS junctions.

Noise spectrum. The current operator is

$$\hat{I}(t_1,x_1)=\frac{ie\hbar}{2m}\left[(\nabla_1-\nabla_1')\sum_\alpha\hat{\psi}_\alpha^\dagger(1)\hat{\psi}_\alpha(1')\right]_{1=1'} \quad (1)$$

where $\hat{\psi}_\alpha$ is the operator of particle field with a spin α. Noise spectrum is defined as a Fourier transform,

$$S(\omega)=\int e^{i\omega\tau}d\tau\overline{\left\langle\left\{\Delta\hat{I}(t-\frac{\tau}{2},x),\Delta\hat{I}(t+\frac{\tau}{2},x)\right\}\right\rangle} \quad (2)$$

where $\Delta\hat{I}\equiv\hat{I}-\langle\hat{I}\rangle$, $\langle\hat{I}\rangle$ is the statistical average current, and $\{\hat{A},\hat{B}\}\equiv(\hat{A}\hat{B}+\hat{B}\hat{A})/2$, while overline means the av-

erage over a long time interval, T_0: $\overline{A} \equiv T_0^{-1}\int_0^{T_0} A(t)\,dt$.

We focus on the low-frequency behavior of the noise correlator, such that $\hbar\omega$ is much smaller than the characteristic energies of the states involved. In this situation, making use of the Bogoliubov transformation one can express the correlator in Eq. (2) through the occupation numbers $f(\epsilon_n)$ of the sub-gap states and matrix elements, L_{mn}, quadratic in current operators:

$$S = -\frac{\pi\hbar^3 e^2}{4m^2}\overline{\sum_{n,m}\delta(\epsilon_{nm}+\hbar\omega)L_{nm}[1-f_1(\epsilon_n)f_1(\epsilon_m)]}\ , \quad (3)$$

$$L_{nm}(x,t) = \{(\nabla_1-\nabla_1')(\nabla_2-\nabla_2')[u_n^*(1)u_m(1') + v_n^*(1)v_m(1')][u_n(2')u_m^*(2)+v_n(2')v_m^*(2)]\}_{1=1'=2=2'}\ . \quad (4)$$

Here u_n, v_n and ϵ_n are the wave functions and energies of the sub-gap states, which have to be found from the Bogoliubov-de Gennes (BdG) equations, $\epsilon_{nm} = \epsilon_n - \epsilon_m$. These quantities depend adiabatically on time t. The matrix elements L_{nm} are symmetric in the transposition $n \leftrightarrow m$. The functions $f(\epsilon_n)$ are the occupation numbers of the subgap states; here we have introduced the odd-in-ϵ combination $f_1(\epsilon) \equiv f(-\epsilon) - f(\epsilon)$. We will see later that the even combination does not appear in our case, $f_2 \equiv 1 - f(\epsilon) - f(-\epsilon) = 0$.

Sub-gap states. To find the matrix elements L_{mn} we solve the BdG equations for $\epsilon < |\Delta|$ modelling the SI-NIS structure as two insulating barriers described by a symmetric δ-function potential with a magnitude I. By adjusting the barrier height I one can account both for the velocity mismatch in the adjacent conductors and for the tunneling of electrons through the interface. The gap $\Delta = |\Delta|e^{i\chi_{R,L}}$ in the right, $x > d/2$, and left, $x < -d/2$, superconductors has $\chi_{R,L} = \pm\phi/2$, respectively, while $\Delta = 0$ in the normal conductor, $-d/2 < x < d/2$. The states depend on the phase parameters $\alpha = k_x d$ and $\beta = \epsilon d/\hbar v_x$, as well as on the unitary scattering matrices[1] $\hat{S}$ at each NIS interface

$$\hat{S} = \begin{pmatrix} S_N e^{i\delta} & S_A e^{i\chi} \\ S_A e^{-i\chi} & S_N e^{-i\delta}\end{pmatrix} \quad (5)$$

which is parameterized through the barrier strength $Z \equiv mI/\hbar^2 k_x$ and the scattering phase $\delta = \arctan 1/Z$. Here k_x and v_x are the electron wave vector and velocity, respectively. See Refs. [4, 5] for more details and expressions for S_N, S_A.

The wave function inside the normal conductor is a linear combination of an incident particle and an incident hole, each experiencing Andreev and normal reflections at the interfaces. For reflections from the right barrier at $x = d/2$ we have

$$\begin{aligned}\begin{pmatrix} u \\ v\end{pmatrix} &= b\left[\hat{u}^> + S_A e^{-i\phi/2}\hat{v}^< + S_N e^{i\delta}\hat{u}^<\right] \\ &\quad + a\left[\hat{v}^> + S_A e^{i\phi/2}\hat{u}^< + S_N e^{-i\delta}\hat{v}^<\right]; \quad (6)\\ \hat{u}^{>,<}(x) &= e^{\pm iq_+ x}\begin{pmatrix}1\\0\end{pmatrix},\ \hat{v}^{<,>}(x) = e^{\pm iq_- x}\begin{pmatrix}0\\1\end{pmatrix},\end{aligned}$$

where $q_\pm = k_x \pm \epsilon/\hbar v_x$. Comparing Eq. (6) with the similar equation for the left barrier at $x = -d/2$ we find

$$\begin{aligned} ae^{i\alpha}\left[e^{-2i\beta} - e^{i\phi}S_A^2 - e^{-2i\alpha'}S_N^2\right] & \\ -2bS_AS_N\cos(\alpha'+\phi/2) &= 0\ , \quad (7)\\ be^{-i\alpha}\left[e^{-2i\beta} - e^{2i\alpha'}S_N^2 - e^{-i\phi/2}S_A^2\right] & \\ -2aS_AS_N\cos(\alpha'+\phi/2) &= 0\ . \quad (8)\end{aligned}$$

Here $\alpha' = \alpha + \delta$. The wave function Eq. (6) is normalized $\int(|u|^2+|v|^2)\,dx = 1$. Defining $S_N = e^{i\gamma}|S_N|$, the solvability of Eqs. (7)–(8) requires [4]

$$|S_N|^2\sin^2\alpha' + |S_A|^2\cos^2(\phi/2) = \sin^2(\beta+\gamma)\ . \quad (9)$$

A long contact has $d \gg \hbar v_x/\Delta$ and a large number of levels $N \sim d\Delta/\hbar v_x \gg 1$. The levels are separated by minigaps at $\phi = 2\pi k$ and $\phi = \pi(2k+1)$ which disappear when $\alpha' = \pi/2 + \pi m$ and $\alpha' = \pi m$, respectively.

Equilibrium noise. For frequencies $\hbar\omega$ much lower than the interlevel spacing $\epsilon_{n,n+1} \sim \hbar v_x/d$, only diagonal elements contribute to Eq. (3) due to the δ functions,

$$\begin{aligned} L_{nn} &= -16k_x^2\left[(|a_n|^2-|b_n|^2)|S_A|^2\right. \\ &\quad \left. + a_n^* b_n S_N S_A^* e^{i\delta - i\phi/2} + a_n b_n^* S_N^* S_A e^{-i\delta+i\phi/2}\right]^2\ .\end{aligned}$$

Using Eqs. (6)–(9) for the cases of nearly ballistic and weakly transparent contacts we obtain, respectively,

$$L_{nn} = -\frac{4k_x^2}{d^2}\begin{cases} 1\ , & Z\to 0,\ |S_N|\to 0; \\ |S_A|^4\dfrac{\sin^2\phi}{\sin^2\alpha'}\ , & Z\to\infty, |S_A|\to 0\,. \end{cases} \quad (10)$$

Putting $f_1(\epsilon) = f_1^{(0)}(\epsilon) + \tilde{f}_1(\epsilon)$ where $f_1^{(0)}(\epsilon) = \tanh(\epsilon/2T)$ is the equilibrium distribution we find

$$S(\omega) = -\frac{\pi\hbar^2 e^2}{8m^2}\delta(\omega)\sum_n \overline{L_{nn}\left[1-[f_1^{(0)}]^2 - 2f_1^{(0)}\tilde{f}_1\right]}. \quad (11)$$

The first two terms in the square brackets in Eq. (11) give the equilibrium thermodynamic noise with $1-[f_1^{(0)}(\epsilon)]^2 = \cosh^{-2}(\epsilon/2T)$. The δ-function in Eq. (11) is broadened by inelastic relaxation processes described by the rate τ^{-1} corresponding to energies $\epsilon \ll \Delta$. Since the interlevel spacing $\epsilon_{n,n+1} \gg \hbar/\tau$ while $\hbar\omega \ll \epsilon_{n,n+1}$ the $\delta(\omega)$ should be replaced with

$$\Lambda(\omega) = \frac{1}{2\pi}\,\frac{\tau^{-1}}{\omega^2 + 1/4\tau^2}\ .$$

For high transparency we get from Eqs. (10)-(11)

$$S_{\rm th}(\omega) = \frac{\pi v_x^2 e^2}{d^2}\Lambda(\omega)\overline{\sum_{n>0}\cosh^{-2}\frac{\epsilon_n}{2T}}\ . \quad (12)$$

If $\hbar v_x/d \ll T \ll \Delta$, the energies $\epsilon \ll \Delta$. Replacing the sum with the integral $(2d/\pi\hbar v_x)\int d\epsilon$ we find

$$S_{\rm th}(\omega) = (4Tv_x e^2/\hbar d)\Lambda(\omega)\ . \quad (13)$$

For a low-transparency junction, $Z \to \infty$, one has $|S_A|^2 = 1/4Z^4$ for $\epsilon \ll \Delta$, and the noise acquires an additional factor $(32Z^8 \sin^2 2\alpha')^{-1}$ as compared to Eq. (13). The current noise in Eq. (13) is associated with thermal fluctuations in the occupancies of the sub-gap states in the same manner as obtained in Ref. [8] for short junctions. However, the spectral density in long junctions is linear in temperature which accounts for the number of excited levels $N_{\rm eff} = 2Td/\pi\hbar v_x$ contributing to the noise.

Non-equilibrium distribution in high-transparency junctions. A dc current at a finite bias voltage appears only due to nonequilibrium quasiparticle distribution. Indeed, in equilibrium the current would be just the supercurrent adiabatically driven by the time-dependent phase difference $\phi = \omega_J t + \phi_0$ and having zero time-average ($\omega_J = 2eV/\hbar$ is the Josephson frequency). In a highly-transparent barrier, particles with $|\epsilon| > |\Delta|$ remain in equilibrium with the heat bath for $eV \ll \Delta$ because they have sufficient time to escape from the double-barrier region and relax in the continuum. However, the time depending phase induces inter-level LZ transitions across the minigaps near $\phi = \pi k$ producing deviation from equilibrium for the sub-gap states. As the phase changes with time, the outermost Andreev levels split off from the continuum and capture particles at energies $\epsilon = \pm|\Delta|$. These quasiparticles can be then excited to the other levels by LZ transitions. The interplay between the LZ transitions and the weak inelastic relaxation produces the nonequilibrium population of the subgap states and leads to a finite dc current.

The kinetic equation for the subgap distribution was recently derived in Ref. [14] under assumption that LZ transitions occur only near the avoided crossings at $\phi = \pi k$. This can be realized if the minigaps as well the bias, eV, are much less than the typical distance $\hbar v_x/d$ between the levels. Only in this case the avoided crossing points are well defined and there are no voltage-induced inter-level transitions elsewhere. These requirements can be met only in almost ballistic contacts, $1-\mathcal{T} \ll 1$, where $\mathcal{T}$ is the transparency of the interface. The kinetic equation also assumes incoherent LZ transitions. Indeed, the inequality $eV \ll \hbar v_x/d$ ensures that the correlation time of the quantum beating between the adjacent Andreev states, $\hbar/|\epsilon_{n+1,n}| \approx d/v_x$, is much shorter than the time $\sim \omega_J^{-1} = \hbar/2eV$ between successive level crossings.

Between the LZ tunnelling events, the distribution function relaxes due to inelastic scattering with the rate τ^{-1}, which is assumed to be energy-independent. Since the even component is absent, $f_2 = 0$, we have $f_1(\epsilon_n) \equiv 1 - 2f(\epsilon_n)$. For low temperatures, $T \ll \hbar v_x/d$, the equilibrium distribution $f_1^{(0)}(\epsilon_n) = \mathrm{sign}\,(\epsilon_n)$. As a result,

$$f_1[\epsilon_n(\phi)] - f_1^{(0)}(\epsilon_n) = \begin{cases} \psi_n e^{-\hbar\phi/2eV\tau}, & 0 < \phi < \pi, \\ \chi_n e^{-\hbar(\phi-\pi)/2eV\tau}, & \pi < \phi < 2\pi. \end{cases}$$

The LZ transitions at $\phi = 2\pi k$ and $\phi = \pi + 2\pi k$ with (constant) probabilities p_0 and p_π, respectively, lead to difference equations for ψ_n and χ_n with constant coefficients[14]. The boundary conditions require that, for the levels moving upwards with the increase in ϕ, the distribution coincides with the equilibrium at $\epsilon = -|\Delta|$, while, for levels moving downwards, the distribution coincides with the equilibrium at $\epsilon = +|\Delta|$. Solution to the difference equations [14] obeys $\psi_{-n} = -\psi_{n+1}$, which implies the property $f_1(\epsilon) = -f_1(-\epsilon)$ used earlier. For $\epsilon_n > 0$ we have $\psi_{n+1} + \psi_n = -2e^{\nu} F(N-n)/F(N)$, where $\nu = \pi\hbar/2eV\tau$ is the degree of inelastic relaxation during the Josephson half-period,

$$\begin{aligned} F(z) &= e^{rz}\left(1 + e^{r} w_+\right) - e^{-rz}\left(1 + e^{-r} w_-\right), \\ w_\pm &= \frac{p_0 e^{\pm r} + p_\pi e^{\mp r} - 2p_0 p_\pi \cosh(r)}{\zeta + p_0 p_\pi (1 - e^{\pm 2r}) + p_0 + p_\pi - 2p_0 p_\pi}, \end{aligned}$$

and $\zeta = e^{2\nu} - 1$. Depending on voltage, ν can be either large or small. For very low voltage, $\nu \gg 1$, the relaxation rate is $r \approx \nu$, and the distribution relaxes quickly. The most interesting case is when the degree of inelastic relaxation is small, $\nu \ll 1$. In this limit, r is given by

$$\sinh^2(r) = \nu(\nu + p_0 + p_\pi - 2p_0 p_\pi)/p_0 p_\pi \,. \qquad (14)$$

The inverse rate r^{-1} describes the energy broadening of the distribution and determines an effective temperature

$$T_{\rm eff} = r^{-1}(d\epsilon_n/dn) = (\pi\hbar v_x/2rd) \qquad (15)$$

which can much exceed the interlevel spacing if $r \ll 1$.

Let $N = 2d\Delta/\pi\hbar v_x$ be the number of sub-gap levels with $\epsilon_n > 0$. For cases (i) $1/N \ll r \ll 1$ and (ii) $r \ll 1/N$ we have

$$\psi_{n+1} + \psi_n = -2 \begin{cases} e^{-rn}, & (i); \\ \dfrac{N + (p_0 + p_\pi - 2p_0 p_\pi)^{-1} - n}{N + (p_0 + p_\pi - 2p_0 p_\pi)^{-1}}, & (ii). \end{cases} \qquad (16)$$

Nonequilibrium noise. The equilibrium noise vanishes if $T \ll \hbar v_x/d$. For high transparency $Z \to 0$ and slow relaxation $\nu \ll 1$ the nonequilibrium part of Eq. (11) is

$$S_{\rm ne}(\omega) = -\frac{2\pi e^2 v_x^2}{d^2} \Lambda(\omega) \sum_{k=0}^{N/2} \left[\psi_{n+1} + \psi_n\right]_{n=2k+1}.$$

Using Eq. (16) one finds

$$\begin{aligned} S_{\rm ne}(\omega) &= (2\pi e^2 v_x^2 N_{\rm eff}/d^2)\Lambda(\omega)\,; \qquad (17) \\ N_{\rm eff} &= \begin{cases} r^{-1}, & (i)\,; \\ \dfrac{N}{2}\,\dfrac{2[N(p_0 + p_\pi - 2p_0 p_\pi)]^{-1} + 1}{[N(p_0 + p_\pi - 2p_0 p_\pi)]^{-1} + 1}, & (ii)\,. \end{cases} \end{aligned}$$

$N_{\rm eff}$ is the number of excited levels. In the case (i) the noise $S_{\rm ne}(\omega)$ has the form of Eq. (13) where the real temperature is replaced with the *effective temperature* $T_{\rm eff} = \pi\hbar v_x N_{\rm eff}/2d$ defined by Eq. (15). This result agrees qualitatively with the low-voltage noise in short

contacts obtained in Ref. [8] if the real temperature there is replaced with $T_{\rm eff}$. The zero-frequency noise is

$$S_{\rm ne}(0) = (4e^2 v_x^2/d^2) N_{\rm eff}\tau = (8T_{\rm eff} e^2 v_x \tau/\pi\hbar d) \ . \quad (18)$$

This noise does not vanish at zero real temperature; on the contrary, it diverges for $\tau \to \infty$ since $N_{\rm eff} \sim N$ and $T_{\rm eff} \sim \Delta$ when $\nu \to 0$. The effective temperature depends on voltage; it decreases exponentially for low voltages and grows linearly for higher voltages (see below).

The dc current calculated in Ref. [14] is

$$I = (ev_x/d) \times \begin{cases} N_{\rm eff}\lambda \ , & (i); \\ N \ , & (ii). \end{cases} \quad (19)$$

The factor $\lambda \equiv \nu/r = N_{\rm eff}\nu$ is found from Eq. (14)

$$\lambda = \sqrt{\frac{p_0 p_\pi}{1 + (p_0 + p_\pi - 2p_0 p_\pi)/\nu}} \leq 1 \ .$$

It is a LZ-controlled efficiency of the non-equilibrium distribution in contributing to the charge transfer through the junction; $\lambda = 1$ if $p_0 = p_\pi = 1$, while $\lambda = 0$ if $p_0 = p_\pi = 0$: there is no dc current if $\lambda \to 0$.

One can write $S_{\rm ne}(0) = 2qI = 2eIF$ where F is the Fano factor, and $q = eF$ is the effective charge $q = 2en/\lambda$. Here $n = v_x\tau/d$ is the number of times which a particle can fly back and forth along the Andreev level trajectory before it escapes due to inelastic scattering. The effective charge is huge $q \gg e$ since $\tau \gg d/v_x$. The enhancement of fluctuating charge for MAR in short junctions has been predicted theoretically in Refs. [8, 10] and confirmed experimentally in Refs. [11, 12]. For a finite bias voltage the charge is enhanced by a factor $n = \Delta/eV$ which is the number of flights of a particle in the normal region before it accumulates the energy sufficient to escape into continuum. Here we predict that, in long junctions, the fluctuating charge is increased by a larger factor $n/\lambda = v_x\tau/d\lambda$ for bias voltages $eV \ll \hbar v_x/d$.

For highly-transparent contacts $1 - \mathcal{T} \ll 1$ and low energies, the probabilities p_0 and p_π of LZ tunneling can be easily calculated. Assuming that $\phi = \omega_J t + \phi_0$ one finds [14] $p_\pi = \exp\left[-(\omega_0/\omega_J)\sin^2\alpha'\right]$ where $\omega_0 = \pi v_x(1-\mathcal{T}^2)/\mathcal{T}d$. For p_0 one replaces $\sin\alpha'$ with $\cos\alpha'$. Therefore, for $\omega_J \ll \omega_0$ the efficiency factor λ is small, leading to enormous enhancement of the effective charge. For $\omega_J \gg \omega_0$ one obtains $p_0 + p_\pi - 2p_0p_\pi = \omega_0/\omega_J$. In the case $Nr \gg 1$ the effective temperature is linear in voltage, $T_{\rm eff} = (\hbar v_x/2d)(\omega_J\tau/\sqrt{1+\omega_0\tau/\pi})$. The LZ efficiency $\lambda = 1/\sqrt{1+\omega_0\tau/\pi}$ is much smaller than unity for $\omega_0\tau \gg 1$. As a result, the effective charge is still much larger than $2en$, namely $q = 2en\sqrt{1+\omega_0\tau/\pi}$.

In conclusion, we have considered both thermal and non-equilibrium low-voltage noise spectrum in long SINIS junctions. The spectrum has a pronounced peak at $\omega = 0$; its intensity diverges at zero temperature, while the width is equal to the inelastic relaxation rate. The spectrum allows one to determine the effective temperature of the sub-gap excitations which remains finite even at zero ambient temperature. At weak inelastic scattering the Fano factor is large; it is determined by LZ tunnelling between the sub-gap states.

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